

Product data sheet

Unit А

А

А

А

V

V

V

ns

ns

ns

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Isolated plastic package
- Low reverse recovery current
- Low thermal resistance •
- Reduces switching losses in associated MOSFET .

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC) •
- Half-bridge/full-bridge switched-mode power supplies •
- Half-bridge lighting ballasts

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 59 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	-	8
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _h ≤ 59 °C; square-wave pulse	-	-	16
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	-	80
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	88
Static chara	acteristics				
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85
		I _F = 8 A; T _j = 25 °C	-	2	2.9
		I _F = 16 A; T _j = 150 °C	-	1.7	2.3
Dynamic ch	naracteristics	· · · · ·			
t _{rr}	reverse recovery time	$ I_{F} = 8 \text{ A}; \text{ V}_{\text{R}} = 400 \text{ V}; \text{ d}I_{\text{F}}/\text{d}t = 500 \text{ A}/\mu\text{s}; \\ T_{j} = 100 ^{\circ}\text{C} $	-	32	40
		$I_F = 1 \text{ A}; \text{V}_\text{R} = 30 \text{V}; \text{d}_\text{F}/\text{d}\text{t} = 50 \text{A}/\mu\text{s}; \\ \text{T}_j = 25 \ ^\circ\text{C}$	-	30	52
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$	-	19	-

T_i = 25 °C; <u>Fig. 5</u>

5. Pinning information

Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K – K – A
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYC8X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC8X-600	BYC8X
	600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 59 °C; square-wave pulse; Fig. 1; Fig. 2	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ; t_p$ = 25 µs; $T_h \leq \ 59 \ ^\circ C;$ squarewave pulse	-	16	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	80	А
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	88	A
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

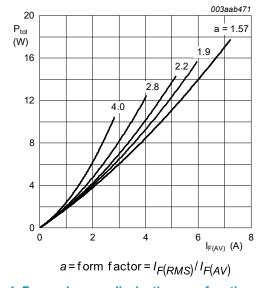


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

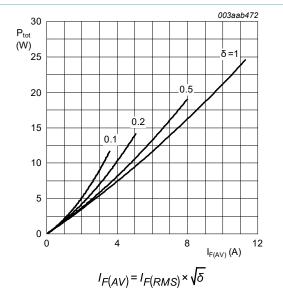


Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 3	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	55	-	K/W

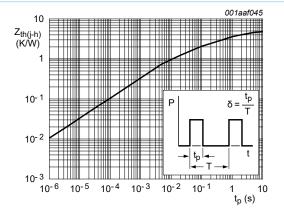


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse width

10. Isolation characteristics

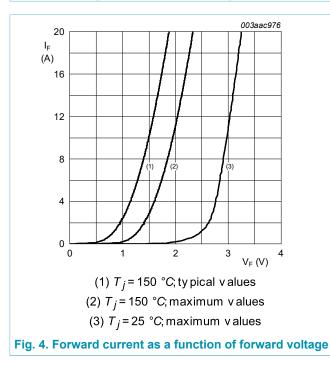
Table 7. Isolati	on characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

Table 7 location observatoristi

Hyperfast power diode

11. Characteristics

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
Static chara	cteristics					
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85	V
		I _F = 8 A; T _j = 25 °C	-	2	2.9	V
		I _F = 16 A; T _j = 150 °C	-	1.7	2.3	V
I _R	reverse current	V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
		V _R = 600 V; T _j = 25 °C	-	9	150	μA
Dynamic ch	aracteristics		· · ·	· · · ·		
t _{rr}	reverse recovery time	I_F = 8 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 100 °C	-	32	40	ns
		I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/µs; T_j = 25 °C	-	30	52	ns
		$ I_F = 8 \text{ A}; \text{ V}_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; \\ T_j = 25 \text{ °C}; \underline{\text{Fig. 5}} $	-	19	-	ns
	peak reverse recovery current	I_F = 10 A; V _R = 400 V; dI _F /dt = 500 A/ µs; T _j = 100 °C	-	9.5	12	A
		I_{F} = 8 A; V_{R} = 400 V; dI_{F}/dt = 50 A/µs; T_{j} = 125 °C	-	1.5	5.5	A
Q _r	recovered charge	I_{F} = 1 A; V_{R} = 100 V; dI_{F}/dt = 100 A/µs; T_{j} = 25 °C	-	12	-	nC
V _{FR}	forward recovery voltage	I _F = 10 A; dI _F /dt = 100 A/µs; T _j = 25 °C; Fig. 6	-	8	10	V



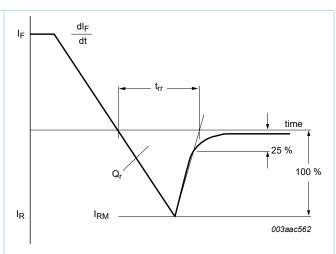


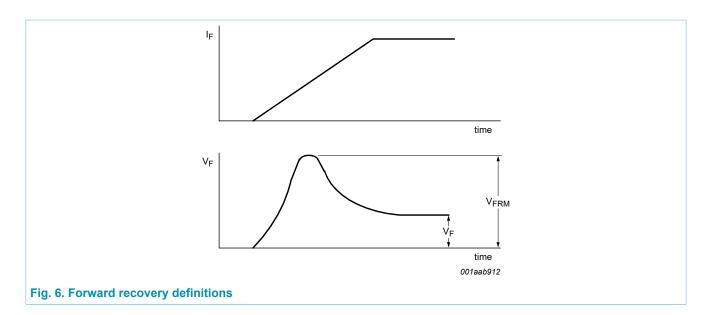
Fig. 5. Reverse recovery definitions; ramp recovery

BYC8X-600

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BYC8X-600

Hyperfast power diode



BYC8X-600



Hyperfast power diode

12. Package outline

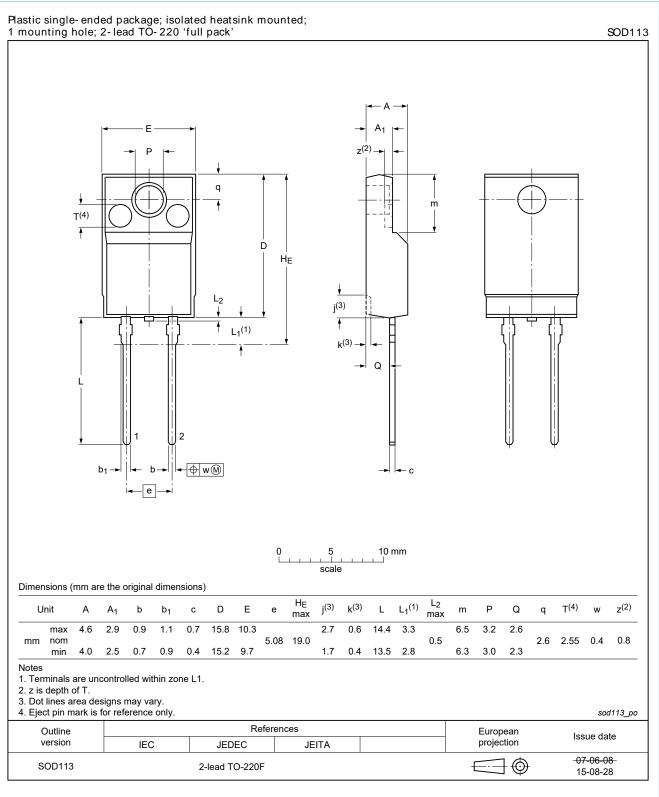


Fig. 7. Package outline TO-220F (SOD113)

BYC8X-600

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Hyperfast power diode

13. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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